

- ..5 Trash

SS9 and S48

Time 2005

	U	I	Inventor	Document ID	Issued	P	Title	Current	Current I	Retrieval	S	C	P	S	Image Data
1			Pomaredo,	US 2004014701A	2004	16	Surface preparation prior to deposition	438/59	257/421.19						US 2004014701A
2			Koyama, M	US 20020149065	2002	2	MIS field effect transistor and method	257/96	257/939;						US 20020149065
3			Pomaredo,	US 2004021620	2004	16	Surface preparation prior to deposition	438/78	257/421.19						US 2004021620
4			Koyama, M	US 2003027171A	2003	2	MIS field effect transistor and method	438/59	257/41;						US 2003027171A
5			Baum, Tho	US 20020187644	2002	2	Source reagent compositions for CVD	438/70	257/421.27						US 20020187644
6			Baum, Tho	US 20020175393	2002	2	Source reagent compositions for CVD	257/50	257/421.27						US 20020175393
7			Pomaredo,	US 20020098627	2002	16	Surface preparation prior to deposition	438/14	257/421.19						US 20020098627
8			Baum, Tho	US 6868938 B2	2005	2	Source reagent compositions for CVD	427/12	427/255.3						US 6868938 B2
9			Koyama, M	US 6809835 B2	2004	2	MIS field effect transistor with metal	257/41;	257/406;						US 6809835 B2
10			Pomaredo,	US 6613695 B2	2003	16	Surface preparation prior to deposition	438/78	257/421.19						US 6613695 B2